IN THE SPECIFICATION

Please amend the paragraph at page 9, lines 8-12, as shown below:

Contact openings are then etched on both sides of the substrate. On the upper side of the substrate, a contact opening 54 ~~59~~ is etched through to the active area of the photodiode anode 32, and a contact opening 60 is etched to the anode guard ring 34. On the underside of the substrate, a contact opening 62 is etched for the bulk connection, i.e. the cathode. This is illustrated in Figure 13.

Please amend the paragraph at page 9, lines 13-22, as shown below:

Aluminium layers 64 are then deposited on both sides of the substrate, and patterned using standard lithographic techniques. The resulting structure is shown in Figure 14. An aluminium layer 64a is formed over at least part of the active region of the guard ring 34 in the opening 60. An aluminium layer 64b is formed over part of the active region 32 of the anode in the opening 59, and an aluminium layer 64c is further formed over a part of the active region 32 of the anode in the opening 54 59, and is connected to the polysilicon layer 56 on the top surface of the substrate. On the under surface of the substrate, an aluminium layer 64d connects to the cathode in the opening 62, and an aluminium layer 64e connects to the polysilicon layer 56.

Please amend the paragraph at page 9, lines 23-28, as shown below:

In an optional step, the material 58 used to fill the hole 48b is removed, as illustrated in Figure 15. The polysilicon provided through the opening 48a provides a conductive via from one substrate surface to another, which conductive via is electrically isolated from the substrate. The hole 48b may be used, in further applications, to provide additional electrical connections through the substrate, by forming additional electrically isolated connections or vias. As illustrated in Figure 15, an additional conductive element 55 is electrically isolated from the polysilicon layer 56 by insulating material 57.